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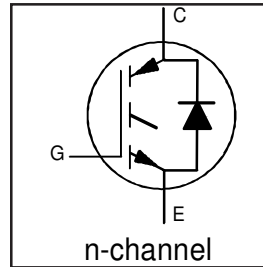
IRG4BC20FD-SPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
 ULTRAFAST SOFT RECOVERY DIODE

Fast CoPack IGBT

Features

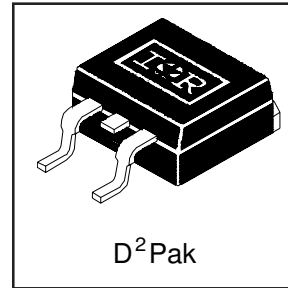
- Fast: Optimized for medium operating frequencies (1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard D²Pak package
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) typ.} = 1.66V$
@ $V_{GE} = 15V, I_C = 9.0A$

Benefits

- Generation 4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs . Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	16	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	9.0	
I_{CM}	Pulsed Collector Current ①	64	
I_{LM}	Clamped Inductive Load Current ②	64	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	8.0	
I_{FM}	Diode Maximum Forward Current	60	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	2.1	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	—	3.5	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)*	—	80	
Wt	Weight	1.44	—	g (oz)

* When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	V _{GE} = 0V, I _C = 250μA
ΔV _{(BR)CES/ΔT_J}	Temperature Coeff. of Breakdown Voltage	—	0.72	—	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	1.66	2.0	V	I _C = 9.0A
		—	2.06	—		I _C = 16A
		—	1.76	—		I _C = 9.0A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)/ΔT_J}	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ^④	2.9	5.1	—	S	V _{CE} = 100V, I _C = 9.0A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 600V
		—	—	1700		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
V _{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	I _C = 8.0A
		—	1.3	1.6		I _C = 8.0A, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q _g	Total Gate Charge (turn-on)	—	27	40	nC	I _C = 9.0A	
Q _{ge}	Gate - Emitter Charge (turn-on)	—	4.2	6.2		V _{CC} = 400V	
Q _{gc}	Gate - Collector Charge (turn-on)	—	9.9	15		V _{GE} = 15V	
t _{d(on)}	Turn-On Delay Time	—	43	—	ns	T _J = 25°C	
t _r	Rise Time	—	20	—		I _C = 9.0A, V _{CC} = 480V	
t _{d(off)}	Turn-Off Delay Time	—	240	360		V _{GE} = 15V, R _G = 50Ω	
t _f	Fall Time	—	150	220		Energy losses include "tail" and diode reverse recovery.	
E _{on}	Turn-On Switching Loss	—	0.25	—		mJ	See Fig. 9, 10, 18
E _{off}	Turn-Off Switching Loss	—	0.64	—			
E _{ts}	Total Switching Loss	—	0.89	1.3			
t _{d(on)}	Turn-On Delay Time	—	41	—	ns	T _J = 150°C, See Fig. 10, 11, 18	
t _r	Rise Time	—	22	—		I _C = 9.0A, V _{CC} = 480V	
t _{d(off)}	Turn-Off Delay Time	—	320	—		V _{GE} = 15V, R _G = 50Ω	
t _f	Fall Time	—	290	—		Energy losses include "tail" and diode reverse recovery.	
E _{ts}	Total Switching Loss	—	1.35	—	mJ		
L _E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package	
C _{ies}	Input Capacitance	—	540	—	pF	V _{GE} = 0V	
C _{oes}	Output Capacitance	—	37	—		V _{CC} = 30V	
C _{res}	Reverse Transfer Capacitance	—	7.0	—		f = 1.0MHz	
t _{rr}	Diode Reverse Recovery Time	—	37	55	ns	T _J = 25°C See Fig. 14	
		—	55	90		T _J = 125°C	
I _{rr}	Diode Peak Reverse Recovery Current	—	3.5	5.0	A	T _J = 25°C See Fig. 15	
		—	4.5	8.0		T _J = 125°C	
Q _{rr}	Diode Reverse Recovery Charge	—	65	138	nC	T _J = 25°C See Fig. 16	
		—	124	360		T _J = 125°C	
di _{(rec)M/dt}	Diode Peak Rate of Fall of Recovery During t _b	—	240	—	A/μs	T _J = 25°C See Fig. 17	
		—	210	—		T _J = 125°C	

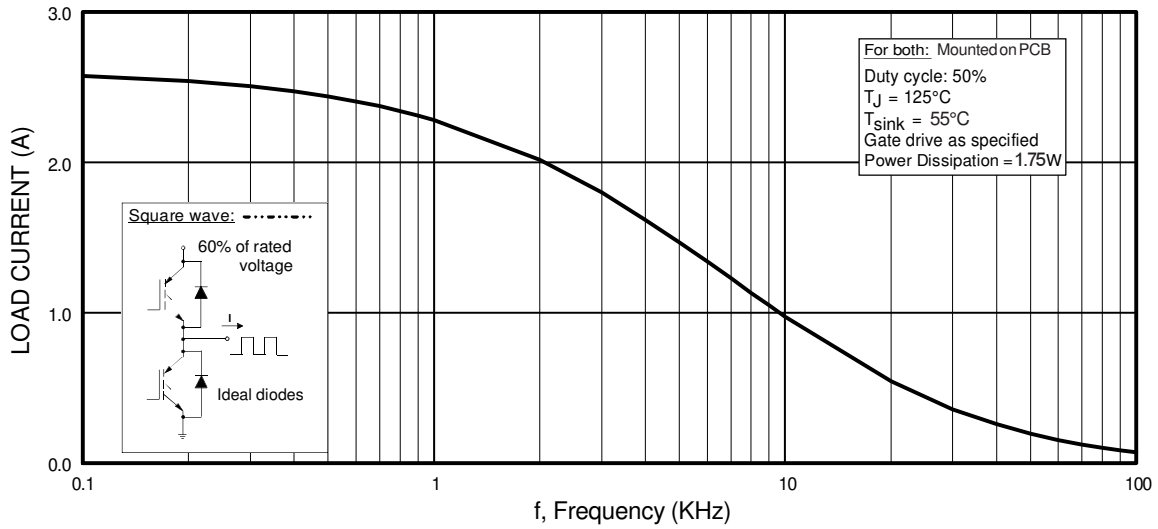


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

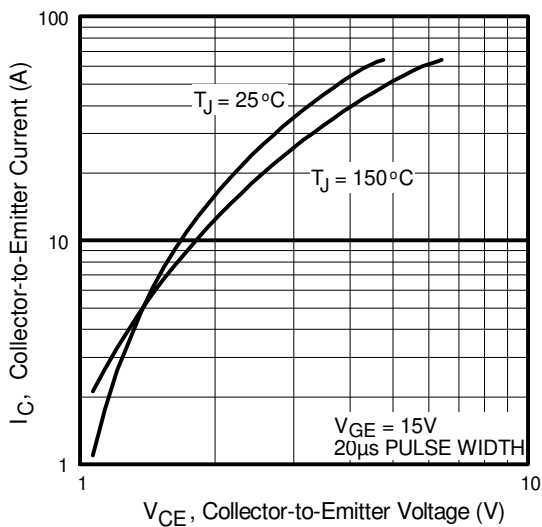


Fig. 2 - Typical Output Characteristics
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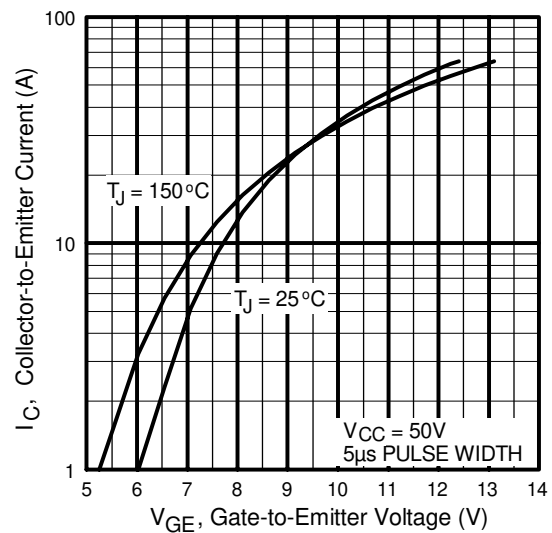


Fig. 3 - Typical Transfer Characteristics

IRG4BC20FD-SPbF

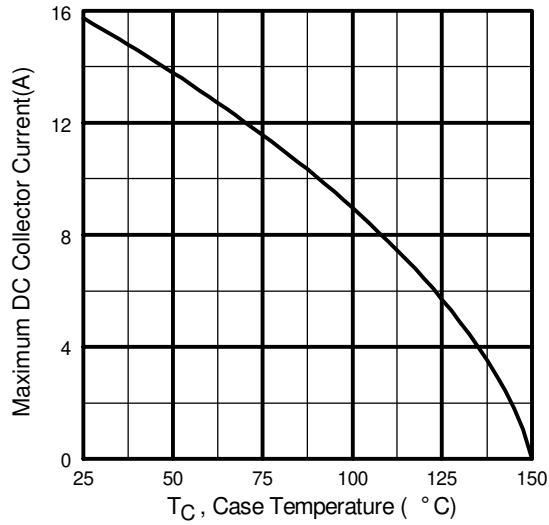


Fig. 4 - Maximum Collector Current vs. Case Temperature

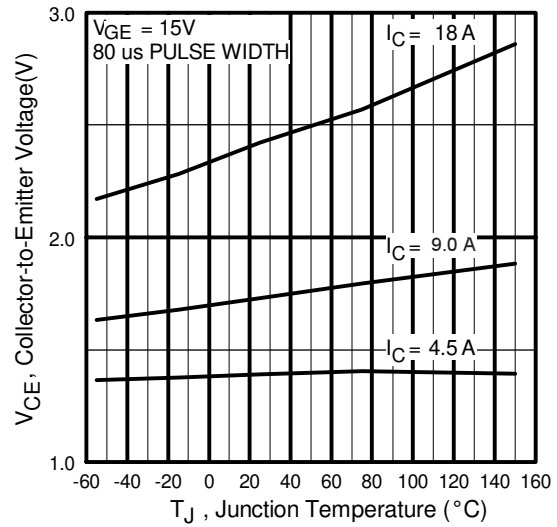


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

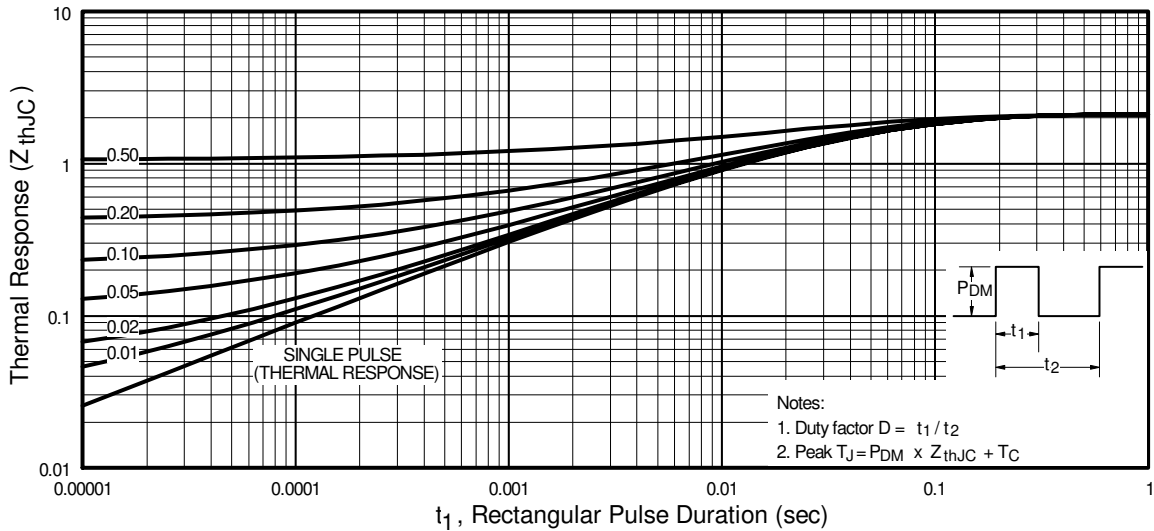


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

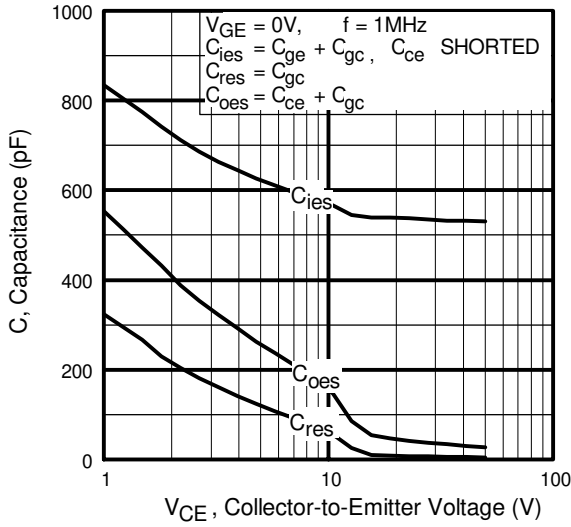


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

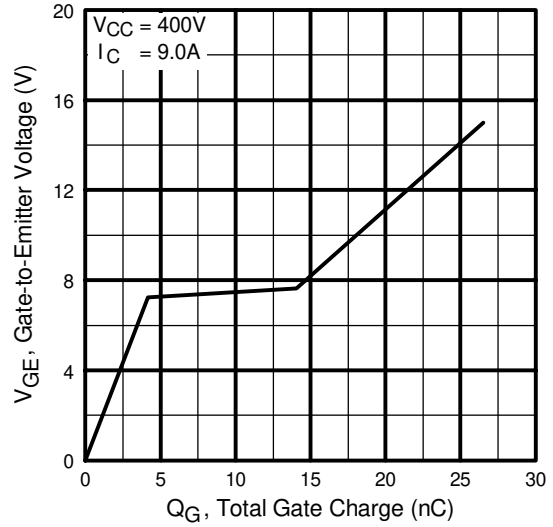


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

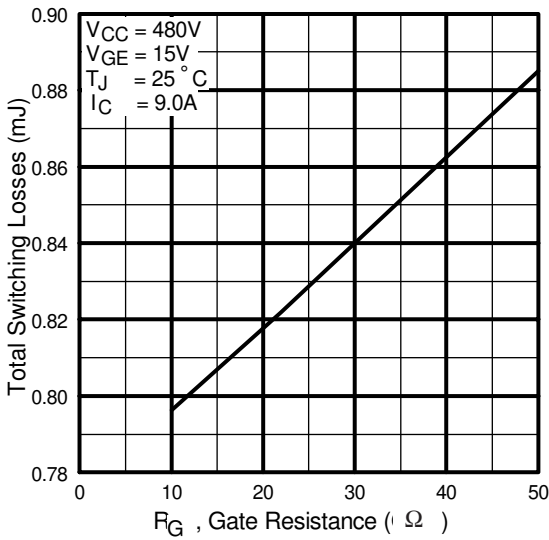


Fig. 9 - Typical Switching Losses vs. Gate Resistance

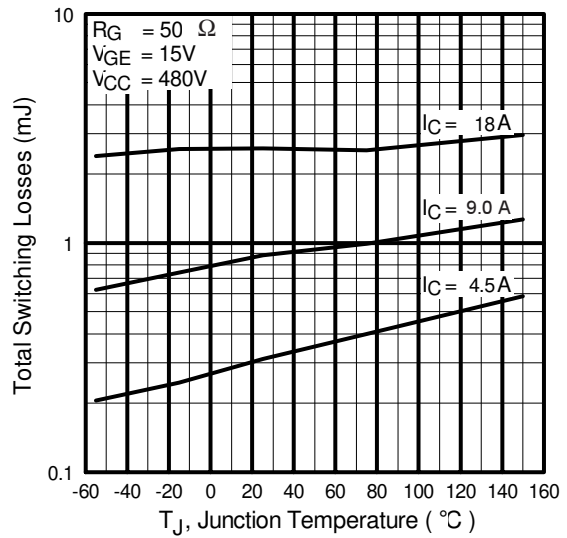


Fig. 10 - Typical Switching Losses vs. Junction Temperature

IRG4BC20FD-SPbF

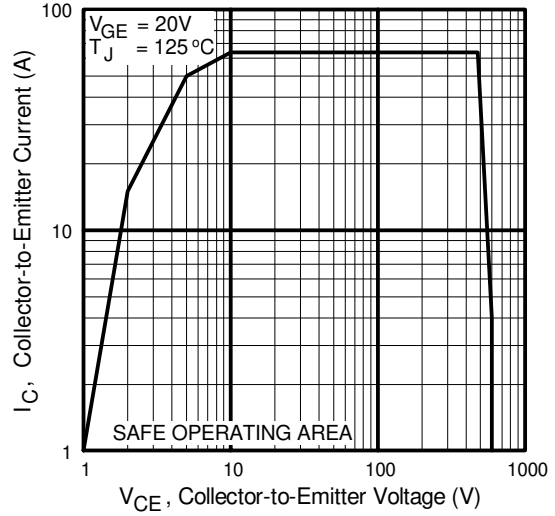
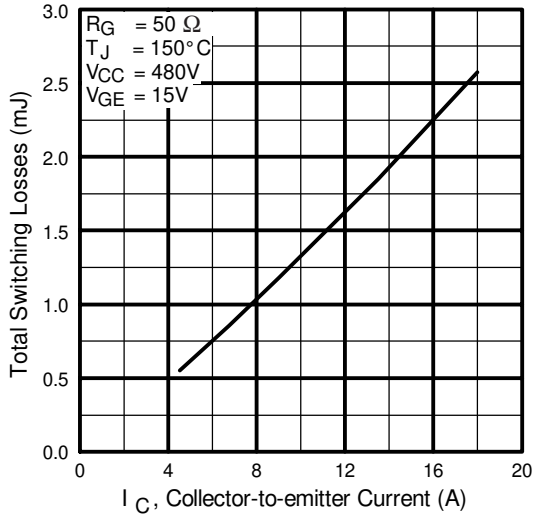


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

Fig. 12 - Turn-Off SOA

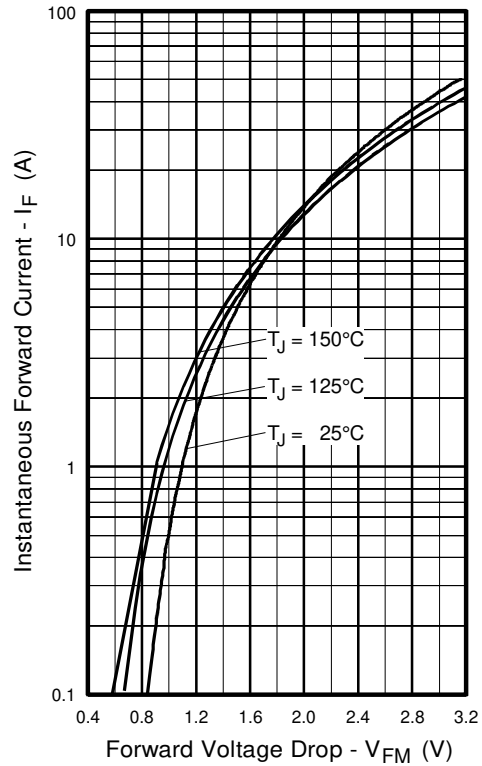


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

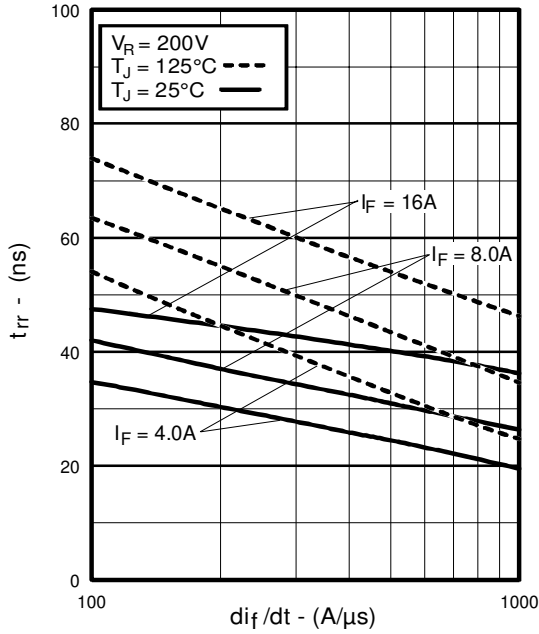


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

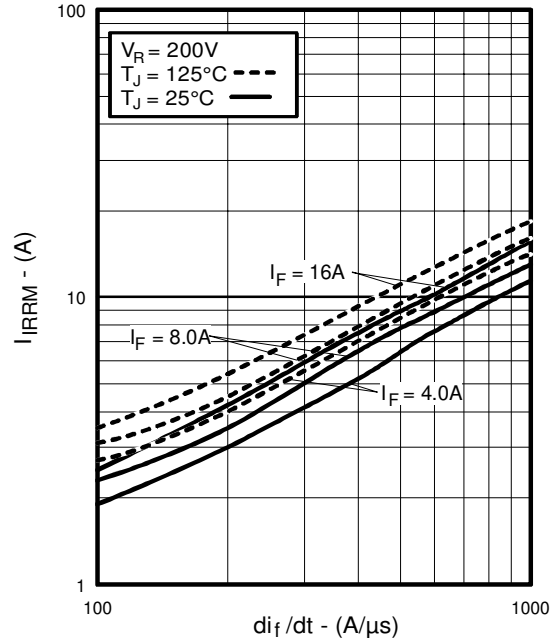


Fig. 15 - Typical Recovery Current vs. di_f/dt

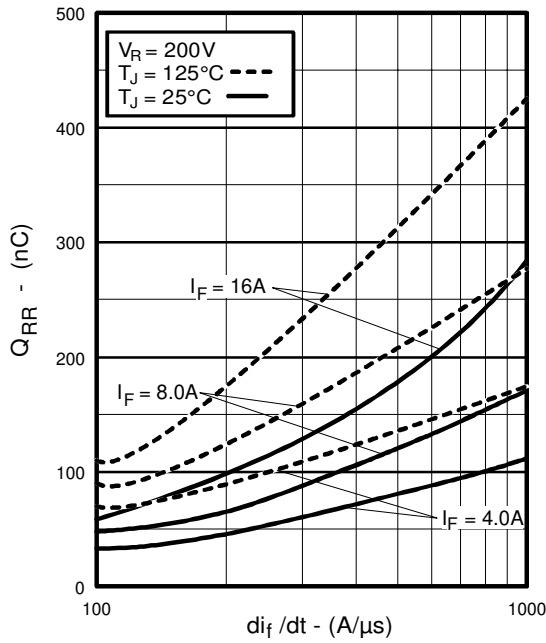


Fig. 16 - Typical Stored Charge vs. di_f/dt

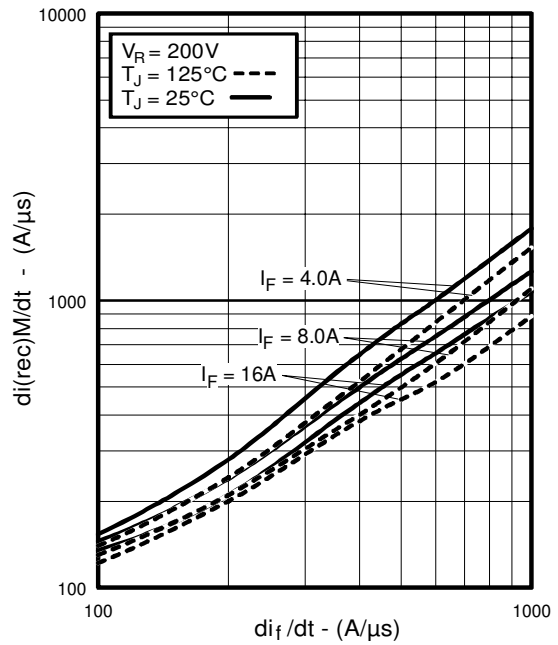


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

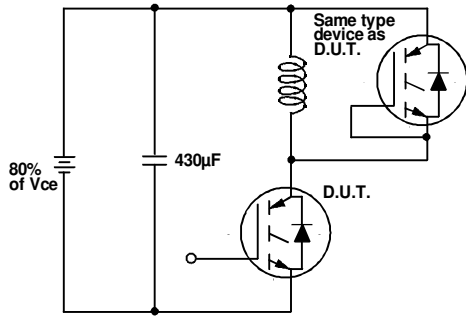


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

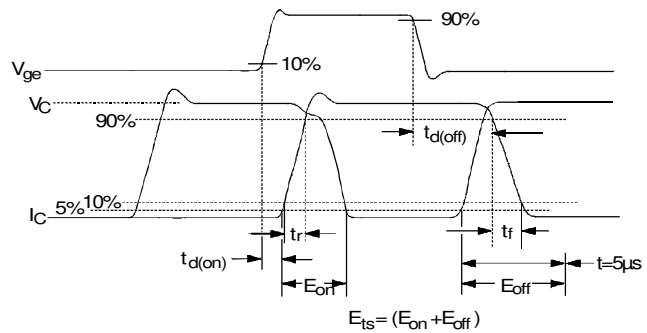


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

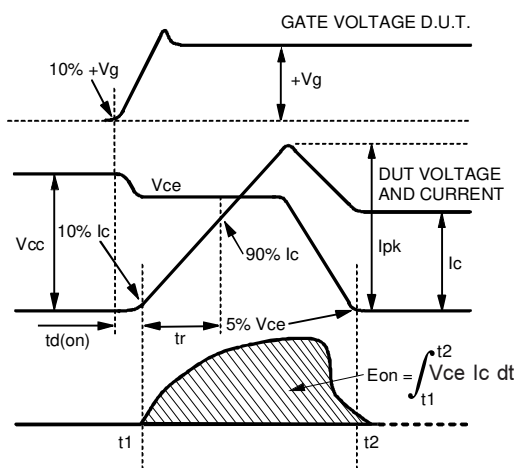


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

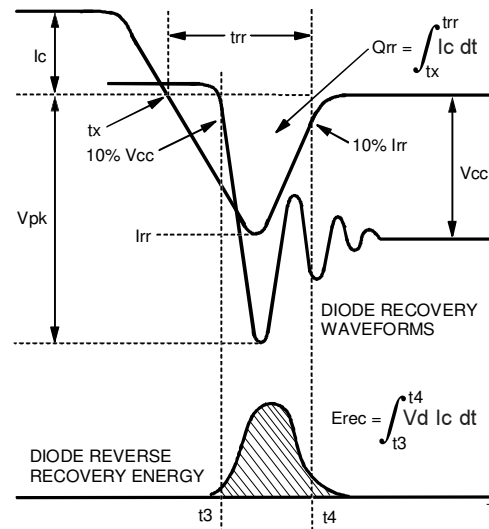


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

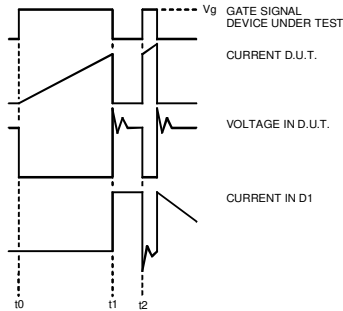


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

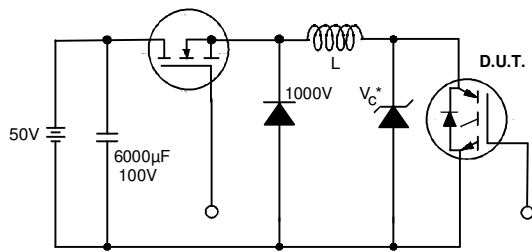


Figure 19. Clamped Inductive Load Test Circuit

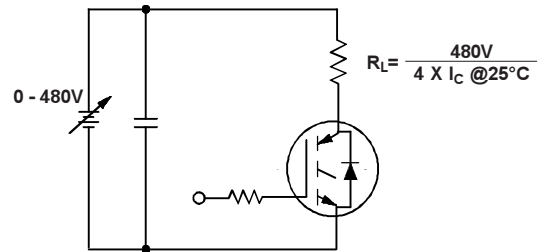
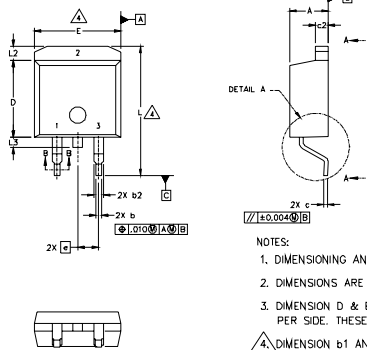
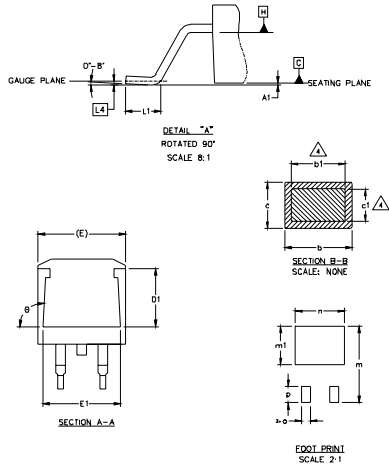


Figure 20. Pulsed Collector Current Test Circuit

IRG4BC20FD-SPbF D²Pak Package Outline

Dimensions are shown in millimeters (inches)

International
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SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	3
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25	BSC	.010	BSC	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

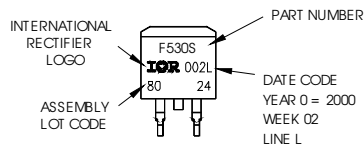
HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

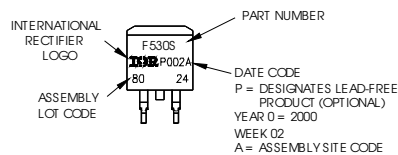
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024 ASSEMBLED ON WW 02, 2000 IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead-Free"

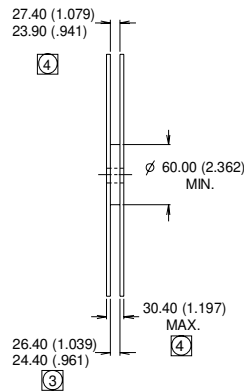
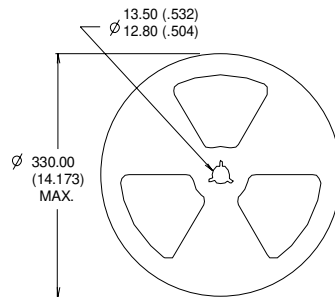
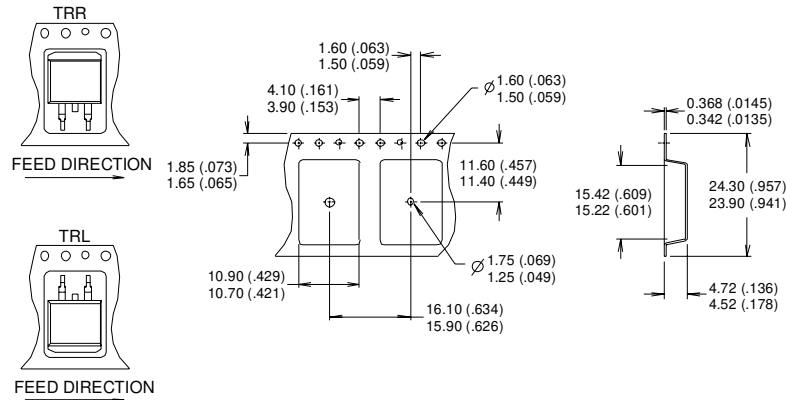


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. COMFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION MEASURED @ HUB.
 4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G = 50\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

Data and specifications subject to change without notice.

International
IR Rectifier

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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>